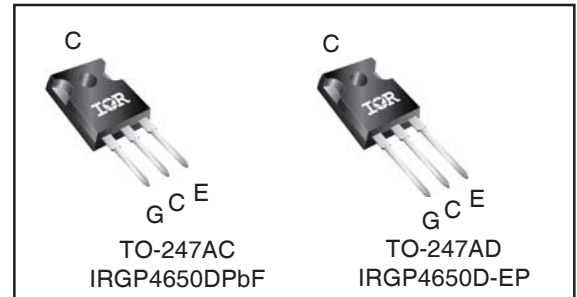
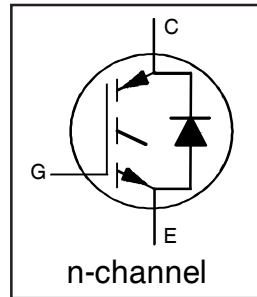


INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

$V_{CES} = 600V$
$I_C = 50A, T_C = 100^\circ C$
$t_{SC} \geq 5\mu s, T_{J(max)} = 175^\circ C$
$V_{CE(on)} \text{ typ.} = 1.60V @ I_C = 35A$



G	C	E
Gate	Collector	Emitter

Applications

- Industrial Motor Drive
- Inverters
- UPS
- Welding

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High efficiency in a wide range of applications and switching frequencies
Square RBSOA and Maximum Junction Temperature 175°C	Improved reliability due to rugged hard switching performance and higher power capability
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent current sharing in parallel operation
5 μs short circuit SOA	Enables short circuit protection scheme
Lead-Free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRGP4650DPbF	TO-247AC	Tube	25	IRGP4650DPbF
IRGP4650D-EPbF	TO-247AD	Tube	25	IRGP4650D-EPbF

Absolute Maximum Ratings

Parameter	Max.	Units
V_{CES} Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$ Continuous Collector Current	76	A
$I_C @ T_C = 100^\circ C$ Continuous Collector Current	50	
I_{CM} Pulse Collector Current, $V_{GE} = 15V$	105	
I_{LM} Clamped Inductive Load Current, $V_{GE} = 20V$ ①	140	
$I_F @ T_C = 25^\circ C$ Diode Continuous Forward Current	76	
$I_F @ T_C = 100^\circ C$ Diode Continuous Forward Current	50	V
I_{FM} Diode Maximum Forward Current ④	140	
V_{GE} Continuous Gate-to-Emitter Voltage	± 20	
	Transient Gate-to-Emitter Voltage	± 30
$P_D @ T_C = 25^\circ C$ Maximum Power Dissipation	268	W
$P_D @ T_C = 100^\circ C$ Maximum Power Dissipation	134	
T_J Operating Junction and	-55 to +175	°C
T_{STG} Storage Temperature Range		
	Soldering Temperature, for 10 sec. Mounting Torque, 6-32 or M3 Screw	

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT) Junction-to-Case (IGBT) ②	—	—	0.56	°C/W
$R_{\theta JC}$ (Diode) Junction-to-Case (Diode) ②	—	—	1.0	
$R_{\theta CS}$ Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$ Junction-to-Ambient (typical socket mount)	—	—	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 100μA ③
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	1.3	—	mV/°C	V _{GE} = 0V, I _C = 1mA (25°C-175°C)
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	1.60	1.90	V	I _C = 35A, V _{GE} = 15V, T _J = 25°C
		—	1.90	—		I _C = 35A, V _{GE} = 15V, T _J = 150°C
		—	2.00	—		I _C = 35A, V _{GE} = 15V, T _J = 175°C
V _{GE(th)}	Gate Threshold Voltage	4.0	—	6.5	V	V _{CE} = V _{GE} , I _C = 1.0mA
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-18	—	mV/°C	V _{CE} = V _{GE} , I _C = 1.0mA (25°C - 175°C)
g _f e	Forward Transconductance	—	25	—	S	V _{CE} = 50V, I _C = 35A, PW = 60μs
I _{CES}	Collector-to-Emitter Leakage Current	—	1.0	70	μA	V _{GE} = 0V, V _{CE} = 600V
		—	770	—		V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C
V _{FM}	Diode Forward Voltage Drop	—	2.0	3.0	V	I _F = 35A
		—	1.4	—		I _F = 35A, T _J = 175°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions		
Q _g	Total Gate Charge (turn-on)	—	69	104	nC	I _C = 35A V _{GE} = 15V V _{CC} = 400V		
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	18	27				
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	29	44				
E _{on}	Turn-On Switching Loss	—	390	508	μJ	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH, T _J = 25°C Energy losses include tail & diode reverse recovery ⑤		
E _{off}	Turn-Off Switching Loss	—	632	753				
E _{total}	Total Switching Loss	—	1022	1261				
t _{d(on)}	Turn-On delay time	—	46	56	ns	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH, T _J = 25°C		
t _r	Rise time	—	33	42				
t _{d(off)}	Turn-Off delay time	—	105	117				
t _f	Fall time	—	44	54				
E _{on}	Turn-On Switching Loss	—	1013	—			μJ	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH, T _J = 175°C Energy losses include tail & diode reverse recovery ⑤
E _{off}	Turn-Off Switching Loss	—	929	—				
E _{total}	Total Switching Loss	—	1942	—				
t _{d(on)}	Turn-On delay time	—	43	—	ns	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH T _J = 175°C		
t _r	Rise time	—	35	—				
t _{d(off)}	Turn-Off delay time	—	127	—				
t _f	Fall time	—	61	—				
C _{ies}	Input Capacitance	—	2113	—	pF	V _{GE} = 0V V _{CC} = 30V f = 1.0Mhz		
C _{oes}	Output Capacitance	—	197	—				
C _{res}	Reverse Transfer Capacitance	—	65	—				
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 175°C, I _C = 140A V _{CC} = 480V, V _p ≤ 600V R _G = 10Ω, V _{GE} = +20V to 0V		
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	V _{CC} = 400V, V _p ≤ 600V R _G = 10Ω, V _{GE} = +15V to 0V		
E _{rec}	Reverse Recovery Energy of the Diode	—	304	—	μJ	T _J = 175°C		
t _{rr}	Diode Reverse Recovery Time	—	120	—	ns	V _{CC} = 400V, I _F = 35A		
I _{rr}	Peak Reverse Recovery Current	—	25	—	A	V _{GE} = 15V, R _G = 10Ω, L = 210μH, L _S = 150nH		

Notes:

- ① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 19μH, R_G = 10Ω.
- ② R_θ is measured at T_J of approximately 90°C.
- ③ Refer to AN-1086 for guidelines for measuring V_{(BR)CES} safely.
- ④ Pulse width limited by max. junction temperature.
- ⑤ Values influenced by parasitic L and C in measurement.

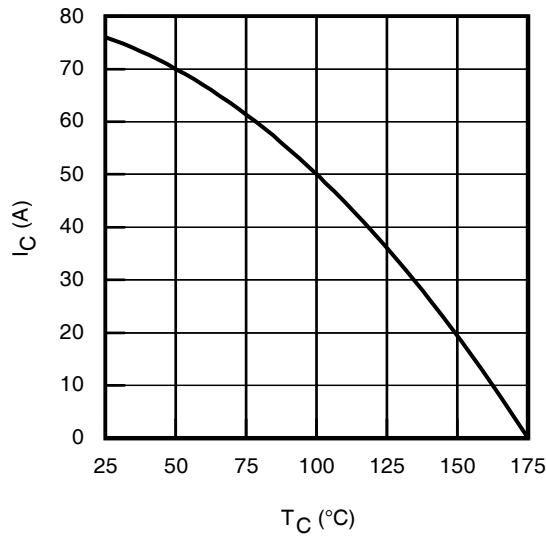


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

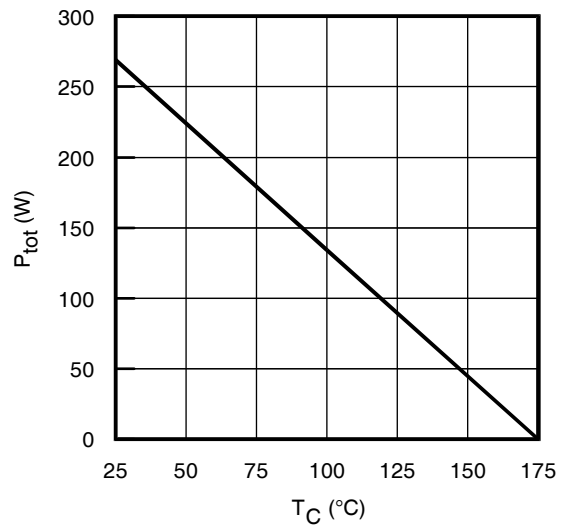


Fig. 2 - Power Dissipation vs. Case Temperature

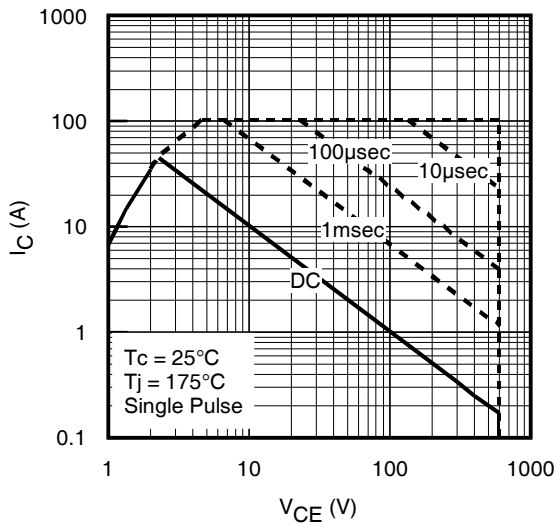


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$



Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 20\text{V}$

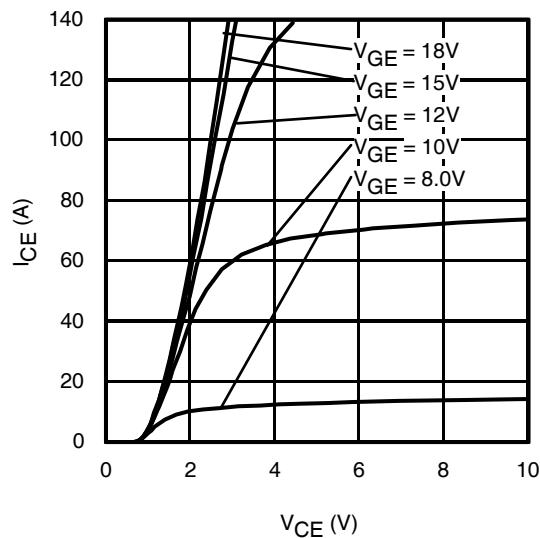


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p \leq 60\mu\text{s}$



Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p \leq 60\mu\text{s}$

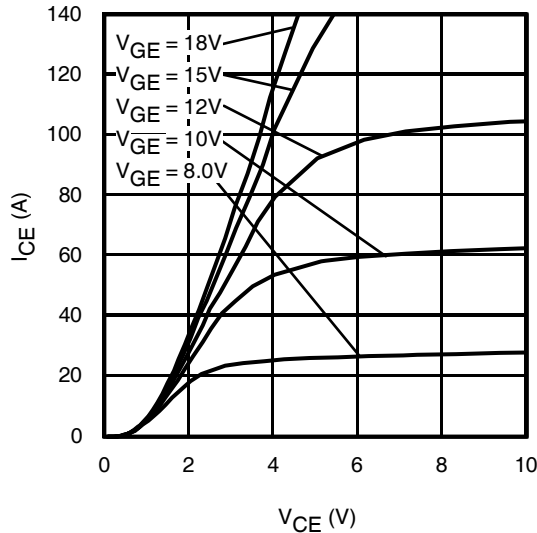


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p \leq 60\mu\text{s}$

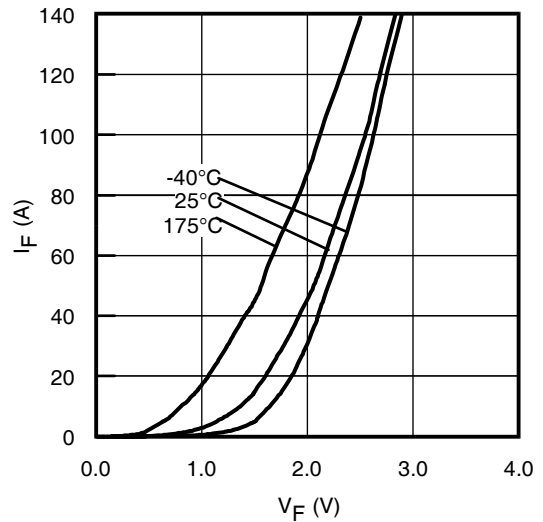


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

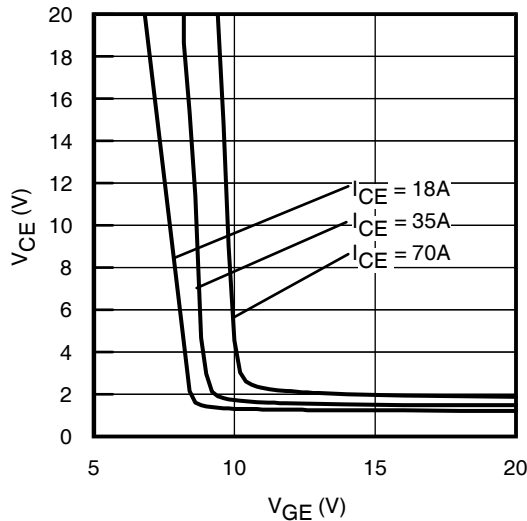


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

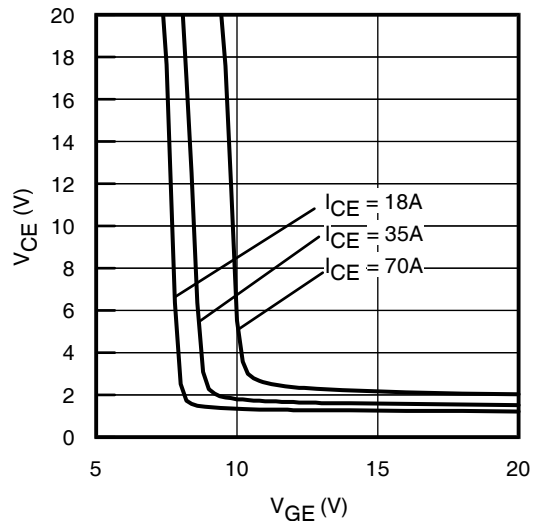


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$



Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

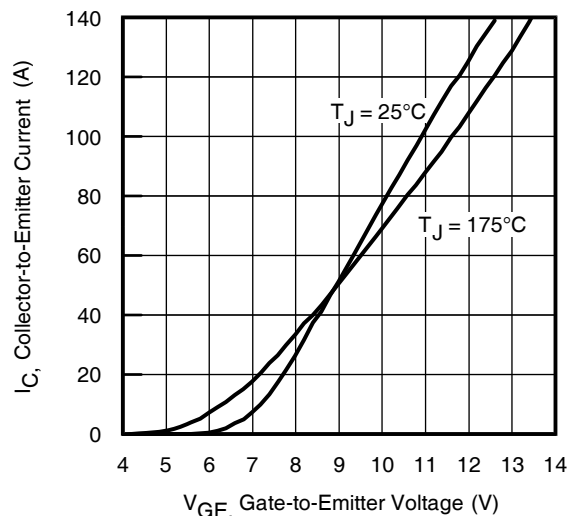


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 60\mu\text{s}$

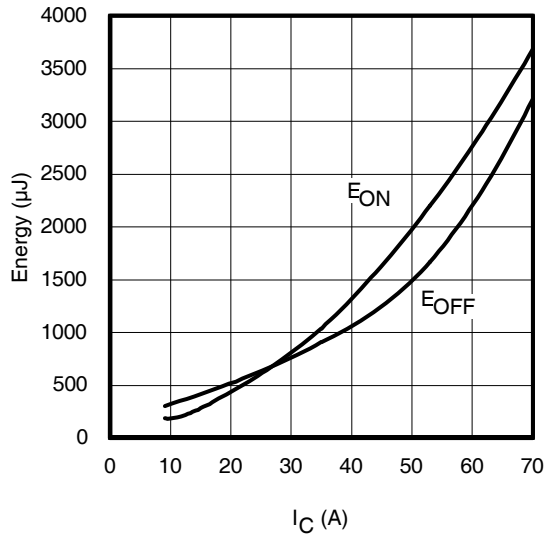
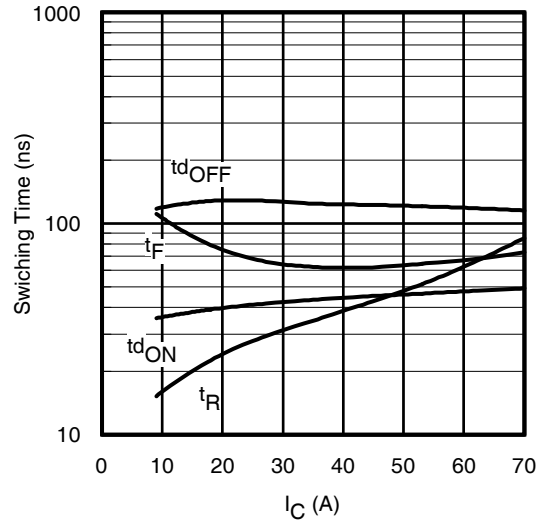
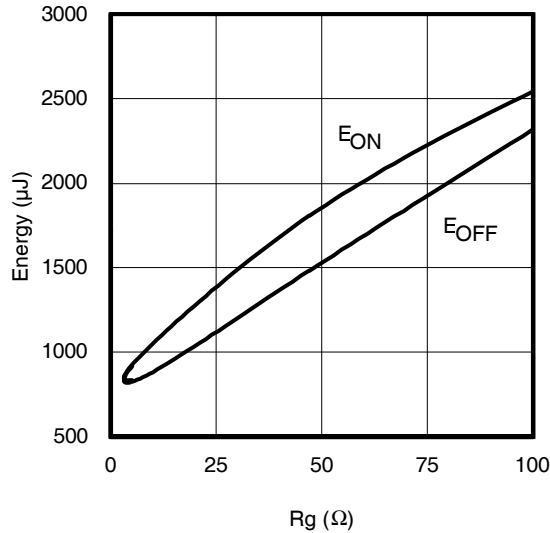
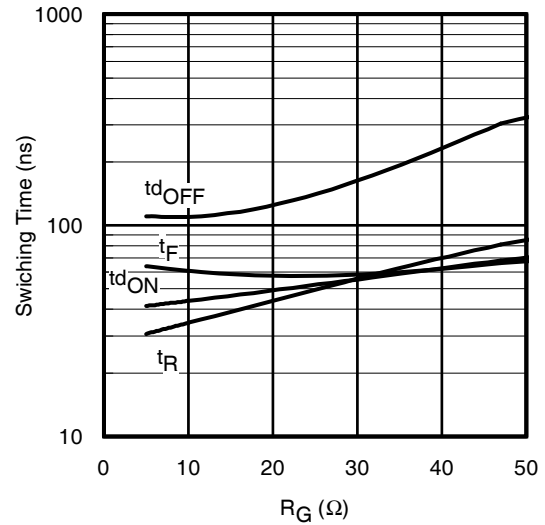
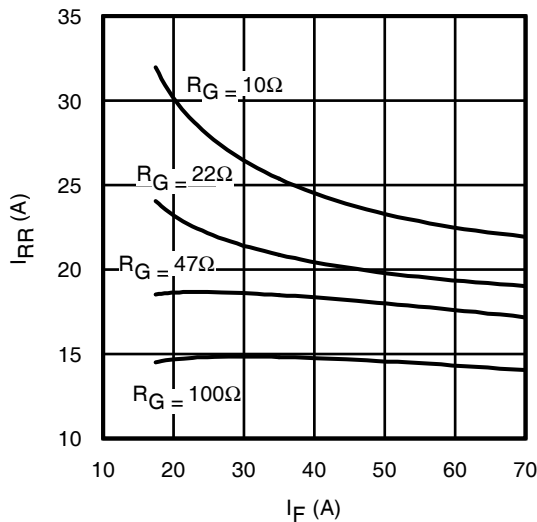
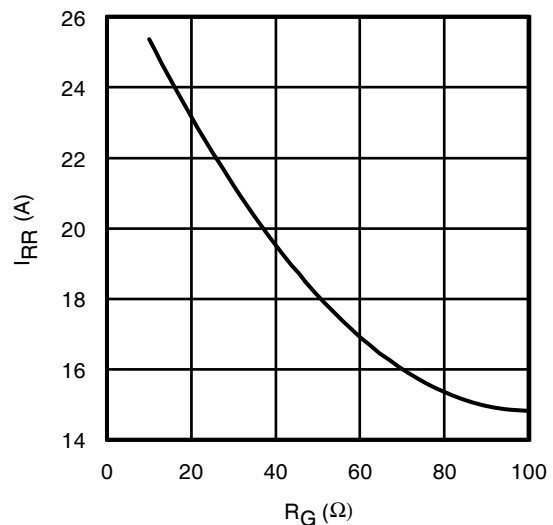

Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}; L = 200\mu\text{H}; V_{CE} = 400\text{V}, R_G = 10\Omega; V_{GE} = 15\text{V}$

Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}; L = 200\mu\text{H}; V_{CE} = 400\text{V}, R_G = 10\Omega; V_{GE} = 15\text{V}$

Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}, I_{CE} = 35\text{A}; V_{GE} = 15\text{V}$

Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}, I_{CE} = 35\text{A}; V_{GE} = 15\text{V}$

Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$



Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 35A$; $T_J = 175^\circ C$

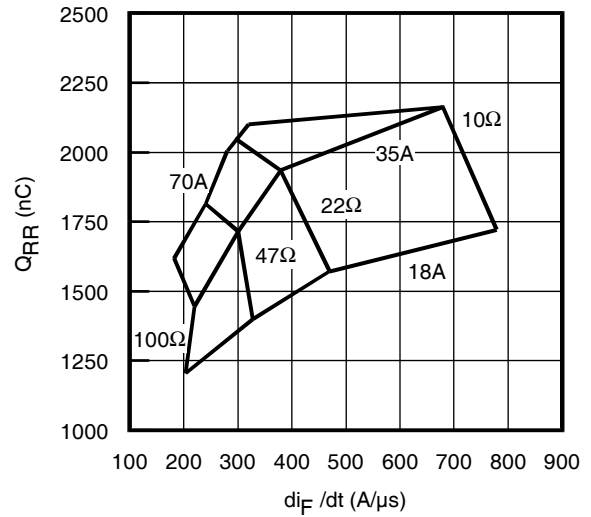


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

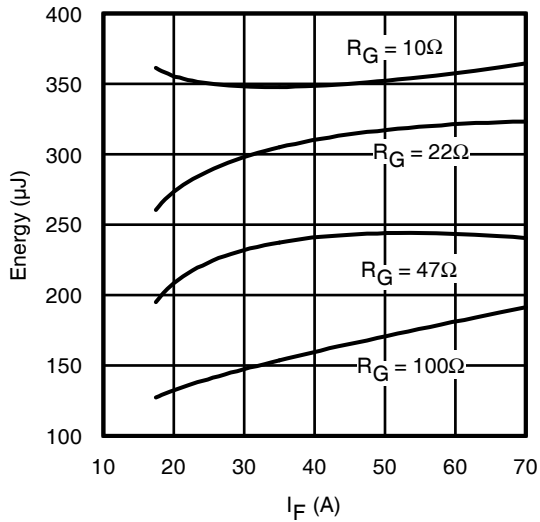


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

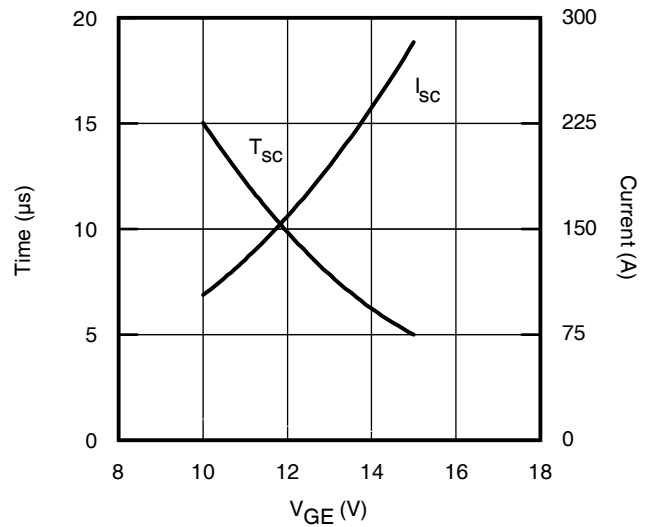


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

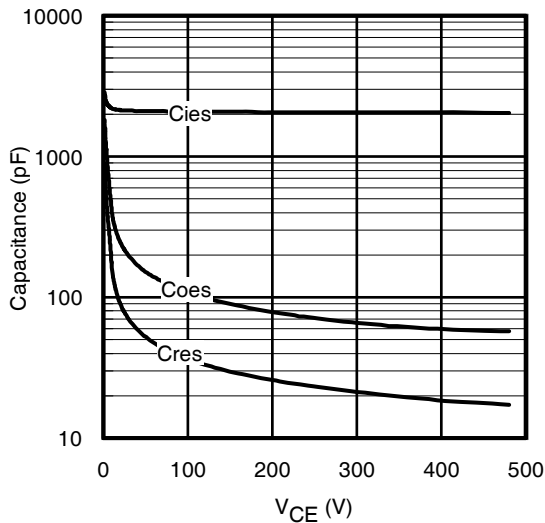


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

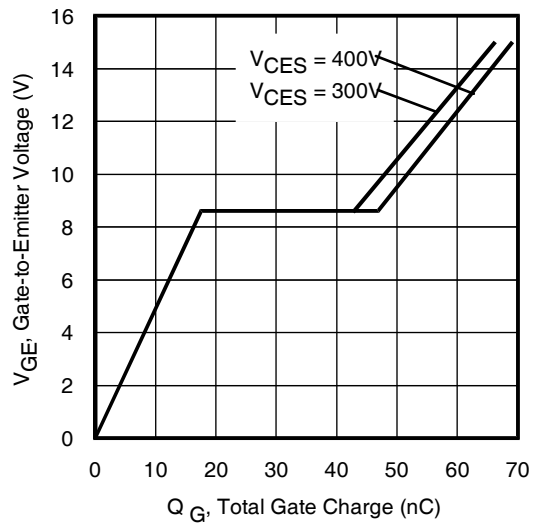
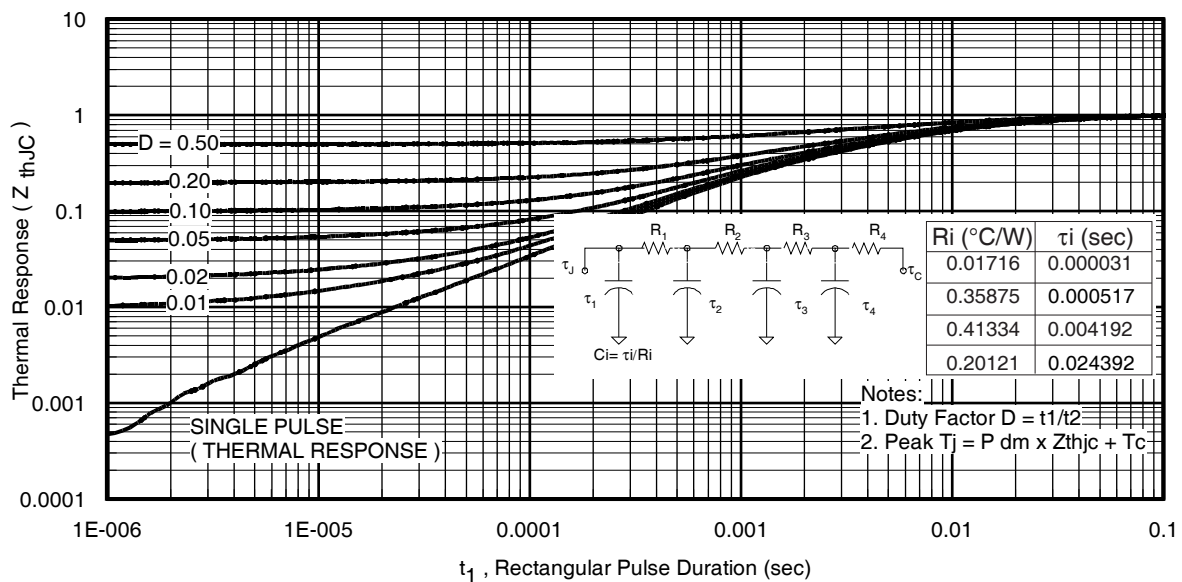
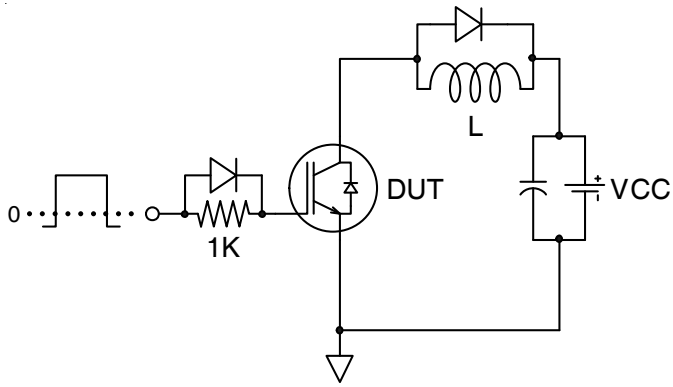
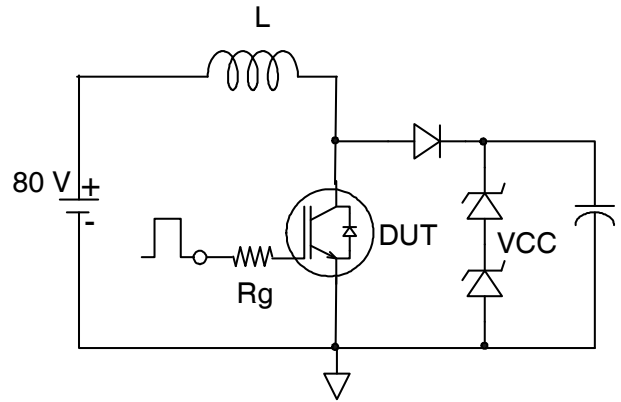
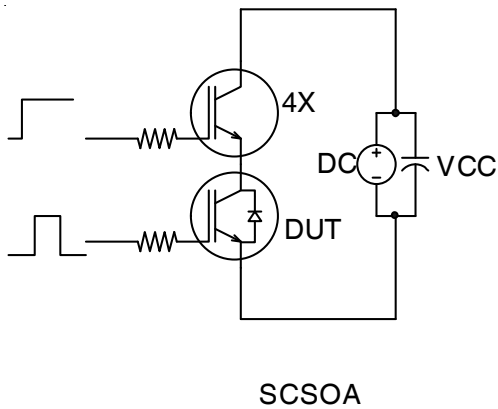
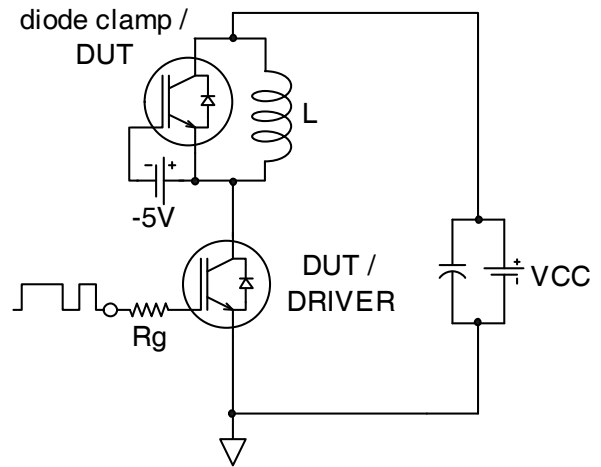
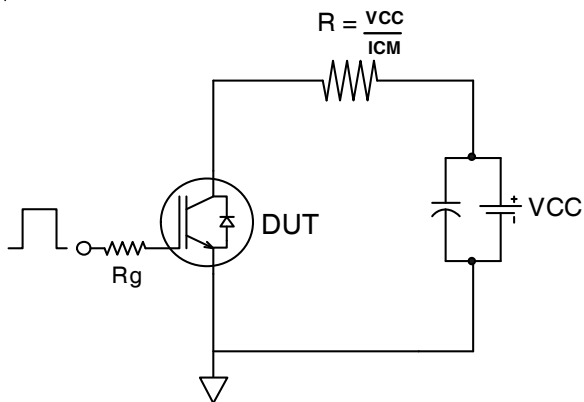
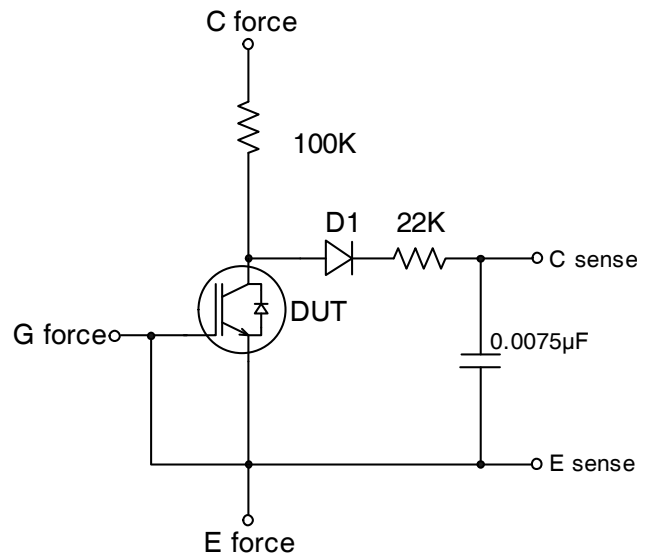


Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 35A$; $L = 740\mu H$


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - S.C. SOA Circuit

Fig.C.T.4 - Switching Loss Circuit

Fig.C.T.5 - Resistive Load Circuit

Fig.C.T.6 - BVCES Filter Circuit

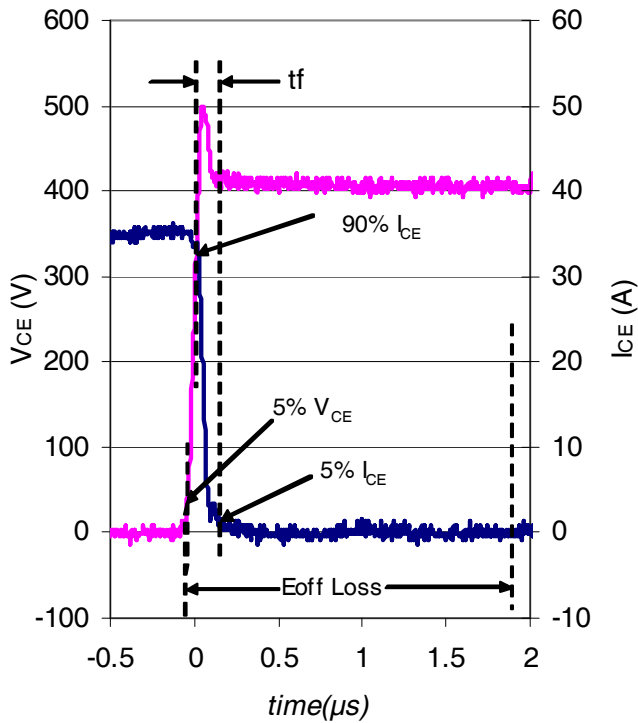


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

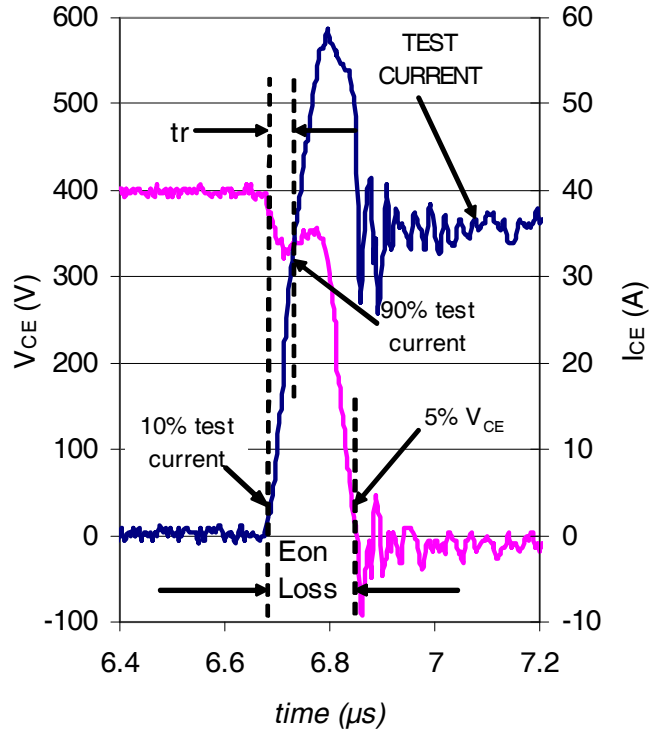


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

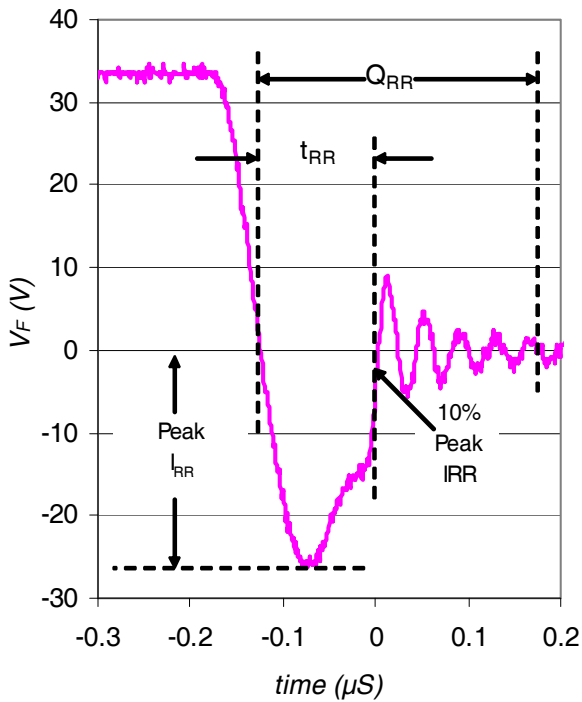


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

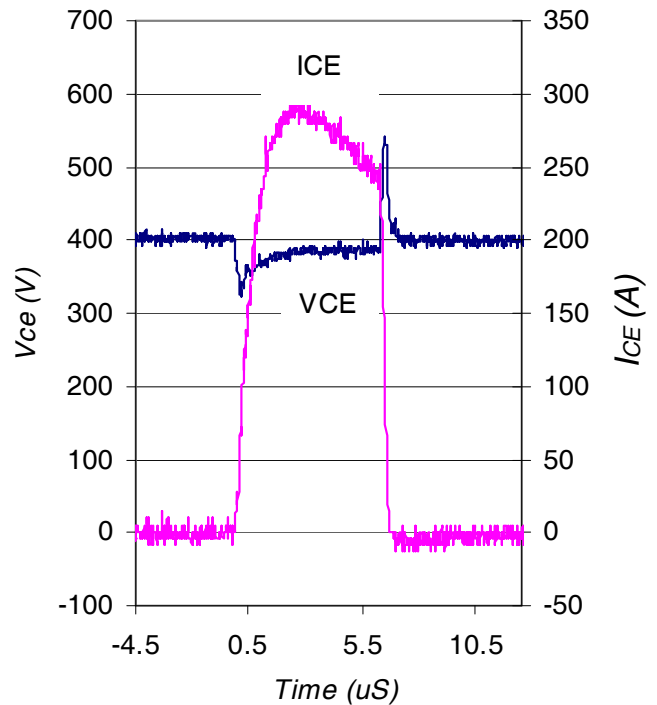
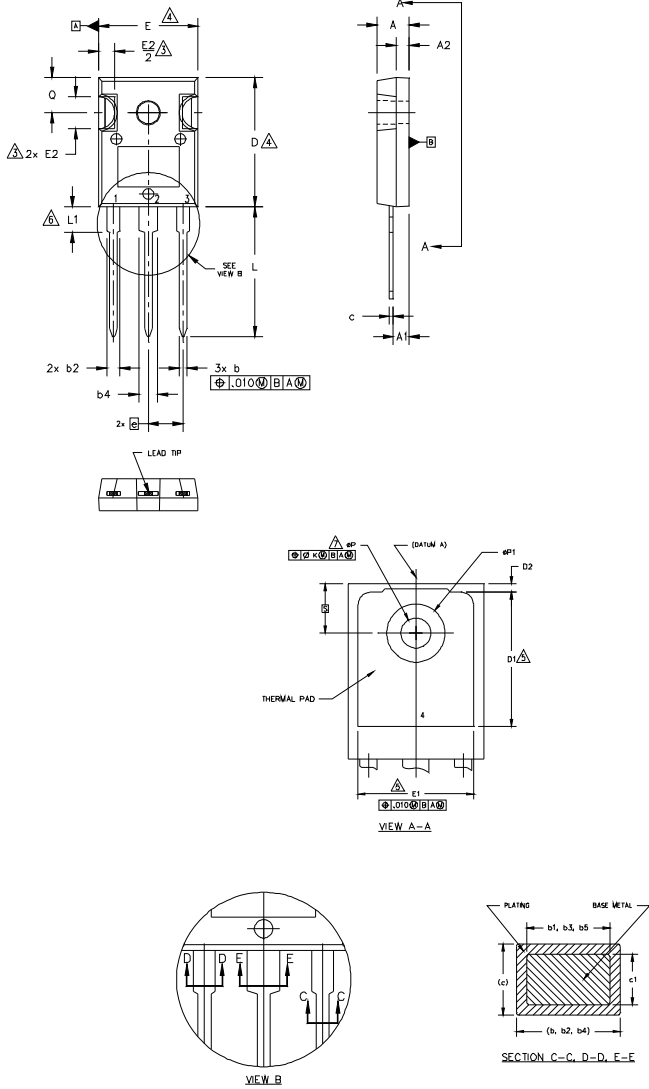


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

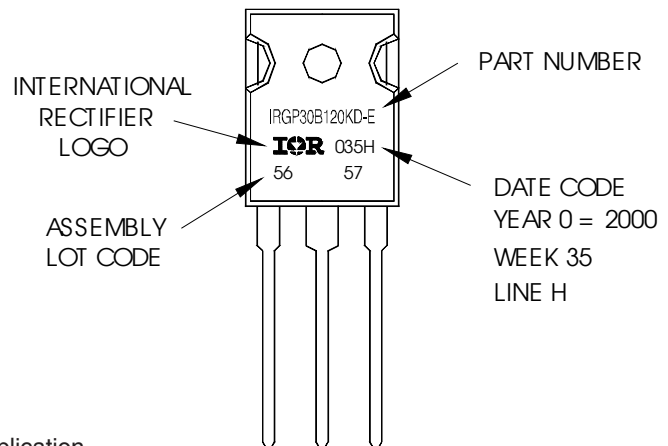
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level	Industrial (per International Rectifier's internal guidelines)	
Moisture Sensitivity Level	TO-247AC	N/A
	TO-247AD	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Highest passing voltage.

Revision History

Date	Comments
11/17/2014	<ul style="list-style-type: none"> • Added note ④ to I_{FM} Diode Maximum Forward Current on page 1. • Added note ⑤ to switching losses test condition on page 2.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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